

150 Watts - 48 Volts, CW Transistor at 2.45GHz

GENERAL DESCRIPTION

The 2425GN-150CW is an internally matched, COMMON SOURCE, class AB, GaN on SiC HEMT transistor capable of providing over 11 dB gain, 150 Watts minimum output power at continuous wave (CW) condition at 2450 MHz band. This hermetically sealed transistor is utilizes gold metallization and eutectic attach to provide highest reliability and superior ruggedness.

Market Application -S-Band ISM applications

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation

Device Dissipation @ 25°C 300 W

Maximum Voltage and Current

Drain-Source Voltage (V_{DSS}) 150 V Gate-Source Voltage (V_{GS}) -8 to +0 V

Maximum Temperatures

Storage Temperature (T_{STG}) -55 to +125° C Operating Junction Temperature +220 °C CASE OUTLINE 55-KR Common Source



ELECTRICAL CHARACTERISTICS @ 25°C

| Symbol | Characteristics | Test Conditions | Min | Тур | Max | Units |
|--------|------------------|-------------------------|-----|------|-----|-------|
| Pout | Output Power | Pin=11.2W Freq=2450 MHz | 150 | 160 | | W |
| Gp | Power Gain | Pin=11.2W Freq=2450 MHz | 11 | 11.6 | | dB |
| ηd | Drain Efficiency | Pin=11.2W Freq=2450MHz | 50 | 55 | | % |
| RL | Return loss | Pin=11.2W Freq=2450 MHz | | | -8 | dB |

Bias Condition: Vdd=+48V, Idq=50mA constant current (Vgs= -2.0 ~ -4.5V typical)

FUNCTIONAL CHARACTERISTICS @ 25°C

| I _{D(Off)} | Drain leakage current | $V_{gS} = -8V, V_D = 50V$ | | 16 | mA |
|---------------------|--------------------------------|----------------------------|-----|-----|----|
| $I_{G(Off)}$ | Gate leakage current | $V_{gS} = -8V, V_D = 0V$ | | 8.4 | mA |
| BV _{DSS} | Drain-source breakdown voltage | $V_{gs} = -8V, I_D = 16mA$ | 150 | | V |

Export Classification: TBD

For the most current data, consult MICROSEMI's website: <u>www.MICROSEMI.com</u> Specifications are subject to change, consult the RFIS factory at (408) 986-8031 for the latest information



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TYPICAL BROAD BAND PERFORMACE DATA

| Frequency | Pin (W) | Pout (W) | ld (A) | RL (dB) | η _D (%) | Gain (dB) | Droop (dB) |
|-----------|------------|-------------|-----------|------------|-----------------------|--------------|---------------|
| 2430 MHz | 11.2 | 165 | 6.14 | -18 | 54 | 11.68 | 0 |
| 2460 MHz | 11.2 | 164 | 6.13 | -14 | 55 | 11.65 | 0 |
| 2490 MHz | 11.2 | 158 | 5.90 | -11 | 54 | 11.49 | 0 |

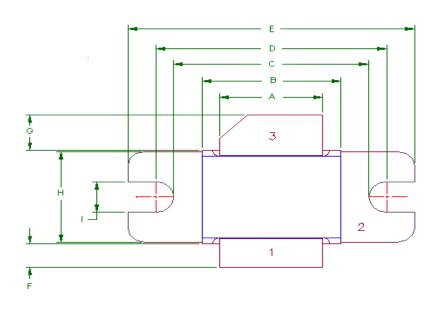
TEST CIRCUIT DIAGRAM

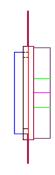
Please contact us for the test circuit

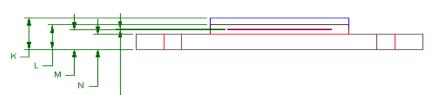


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55-KR PACKAGE DIMENSION







| 1 | = | Gate |
|---|---|--------|
| 2 | = | Source |
| 3 | = | Drain |

| Dimension | Min (mil) | Min (mm) | Max (mil) | Max (mm) |
|-----------|-----------|----------|-----------|----------|
| Α | 370 | 9.40 | 372 | 9.44 |
| В | 498 | 12.65 | 500 | 12.7 |
| С | 700 | 17.78 | 702 | 17.83 |
| D | 830 | 21.08 | 832 | 21.13 |
| E | 1030 | 26.16 | 1032 | 26.21 |
| F | 101 | 2.56 | 102 | 2.59 |
| G | 151 | 3.84 | 152 | 3.86 |
| H | 385 | 9.78 | 387 | 9.83 |
| I | 130 | 3.30 | 132 | 3.35 |
| J | 003 | .076 | 004 | 0.10 |
| K | 135 | 3.43 | 137 | 3.48 |
| L | 105 | 2.67 | 107 | 2.72 |
| M | 085 | 2.16 | 86 | 2.18 |
| N | 065 | 1.65 | 66 | 1.68 |

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Revision History

| Revision Level / Date | Para. Affected | Description |
|-----------------------|----------------|-----------------------------|
| 0.1 / April 8, 2014 | - | Initial Preliminary Release |

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